MDP4N60/MDF4N60

N-Channel MOSFET 600V, 4.6A, 2.0Ω

General Description

These N-channel MOSFET are produced using advanced MagnaChip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

These devices are suitable device for SMPS, high Speed switching and general purpose applications.

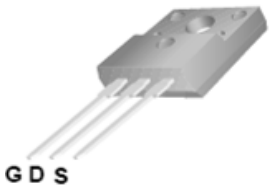
Features

- V_{DS} = 600V
- I_D = 4.6A @ V_{GS} = 10V
- $R_{DS(ON)}$ ≤ 2.0Ω @ V_{GS} = 10V

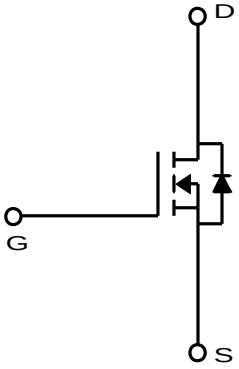
Applications

- Power Supply
- PFC
- High Current, High Speed Switching

TO-220
MDP Series



TO-220F
MDF Series



Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	MDP4N60	MDF4N60	Unit
Drain-Source Voltage		V_{DSS}	600		V
Gate-Source Voltage		V_{GSS}	±30		V
Continuous Drain Current	T_C=25°C	I_D	4.6	4.6*	A
	T_C=100°C		2.9	2.9*	A
Pulsed Drain Current(1)		I_{DM}	18.4	18.4*	A
Power Dissipation	T_C=25°C	P_D	92.5	34.7	W
	Derate above 25 °C		0.74	0.28	W/ °C
Repetitive Avalanche Energy(1)		E_{AR}	9.25		mJ
Peak Diode Recovery dv/dt(3)		dv/dt	4.5		V/ns
Single Pulse Avalanche Energy(4)		E_{AS}	170		mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150		°C

* Id limited by maximum junction temperature

Thermal Characteristics

Characteristics	Symbol	MDP4N60	MDF4N60	Unit
Thermal Resistance, Junction-to-Ambient(1)	$R_{\theta JA}$	62.5	62.5	°C/W
Thermal Resistance, Junction-to-Case(1)	$R_{\theta JC}$	1.35	3.6	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDP4N60TH	-55~150°C	TO-220	Tube	Halogen Free
MDF4N60TH	-55~150°C	TO-220F	Tube	Halogen Free
MDP4N60TP	-55~150°C	TO-220	Tube	Pb Free
MDF4N60TP	-55~150°C	TO-220F	Tube	Pb Free

Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	600	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0	-	5.0	
Drain Cut-Off Current	I_{DSS}	V_{DS} = 600V, V_{GS} = 0V	-	-	1	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V	-	-	100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 2.3A		1.7	2.0	Ω
Forward Transconductance	g_{fs}	V_{DS} = 30V, I_D = 2.3A	-	4	-	S
Dynamic Characteristics						
Total Gate Charge	Q_g	V_{DS} = 480V, I_D = 4.6A, V_{GS} = 10V(3)	-	12.1	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	
Gate-Drain Charge	Q_{gd}		-	4.4	-	
Input Capacitance	C_{iss}	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	-	506	660	pF
Reverse Transfer Capacitance	C_{rss}		-	2.3	3	
Output Capacitance	C_{oss}		-	58	75	
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 10V, V_{DS} = 300V, I_D = 4.6A, R_G = 25Ω(3)	-	12	-	ns
Rise Time	t_r		-	20	-	
Turn-Off Delay Time	$t_{d(off)}$		-	27	-	
Fall Time	t_f		-	20	-	
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I_S		-	4.6	-	A
Source-Drain Diode Forward Voltage	V_{SD}	I_S = 4.6A, V_{GS} = 0V	-	-	1.4	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 4.6A, dI/dt = 100A/μs(3)	-	243	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	1.5	-	μC

Note :

1. Pulse width is based on $R_{\theta JC}$ & $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.
2. Pulse test: pulse width ≤300us, duty cycle≤2%, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
3. I_{SD} ≤4.6A, di/dt≤200A/us, V_{DD}=50V, R_g =25Ω, Starting T_J=25°C
4. L=14.8mH, I_{AS}=4.6A, V_{DD}=50V, R_g =25Ω, Starting T_J=25°C,

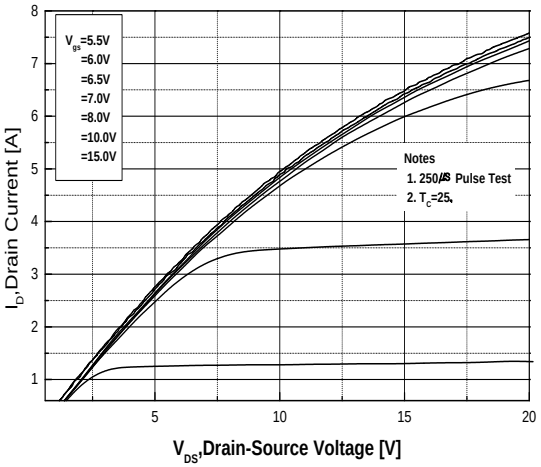


Fig.1 On-Region Characteristics

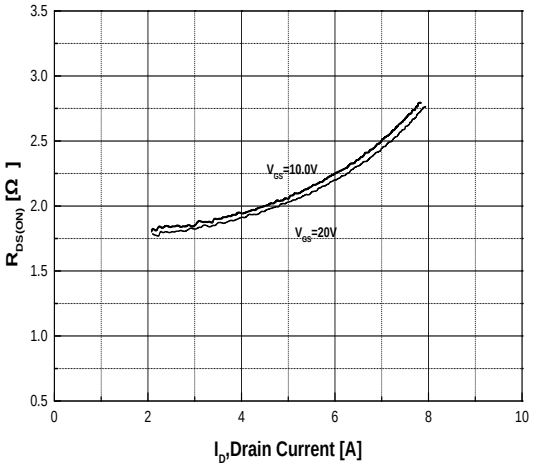


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

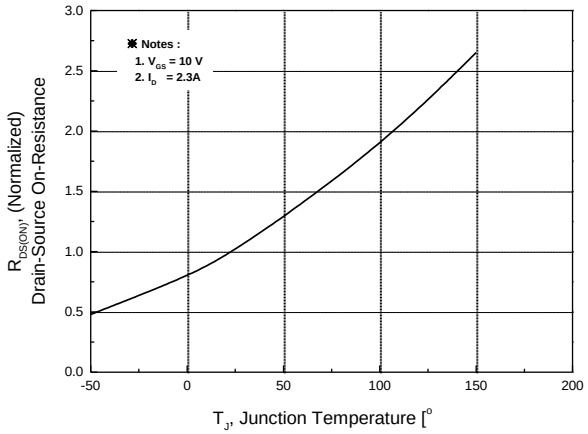


Fig.3 On-Resistance Variation with Temperature

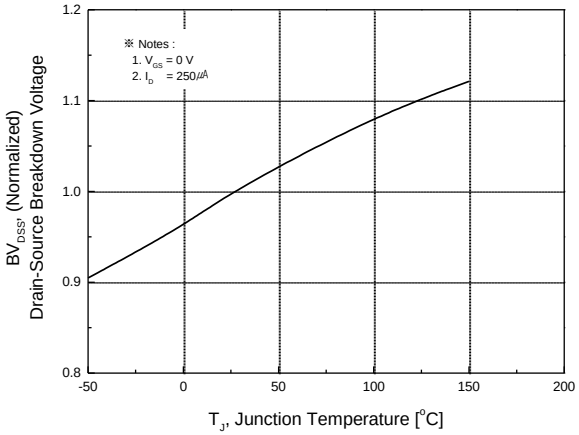


Fig.4 Breakdown Voltage Variation vs. Temperature

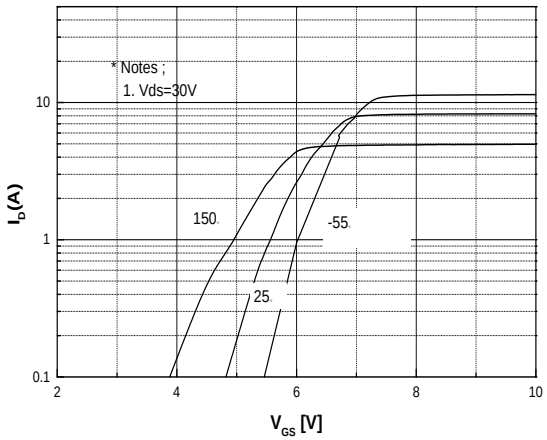


Fig.5 Transfer Characteristics

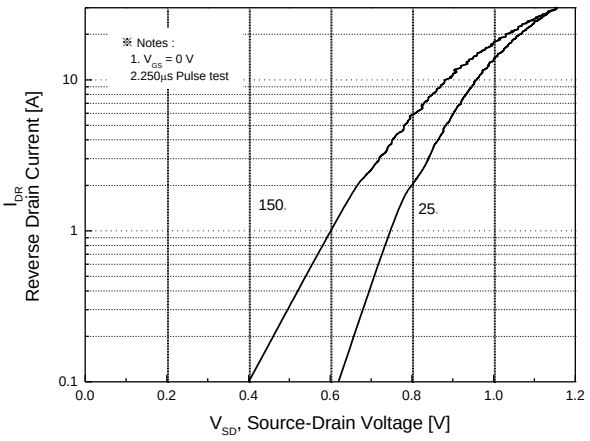


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

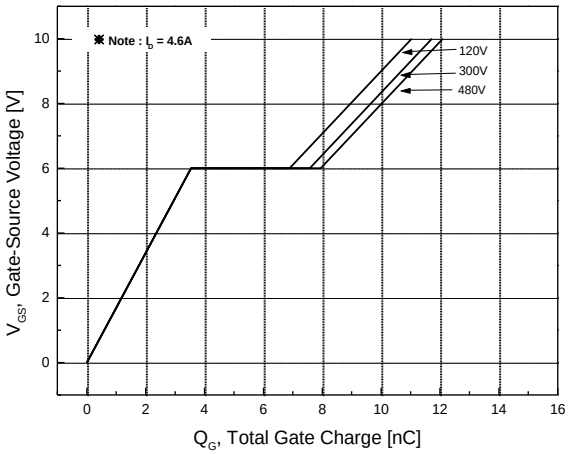


Fig.7 Gate Charge Characteristics

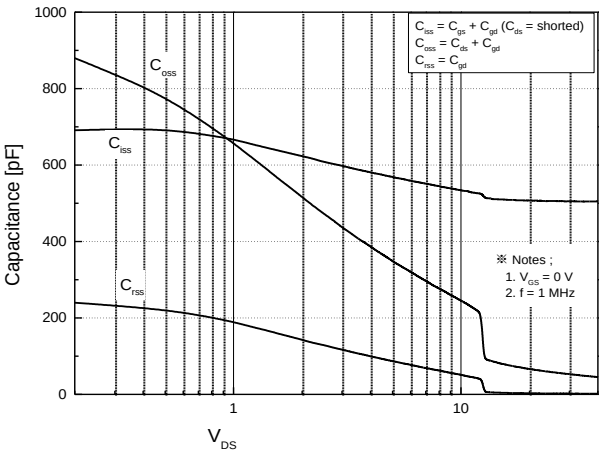


Fig.8 Capacitance Characteristics

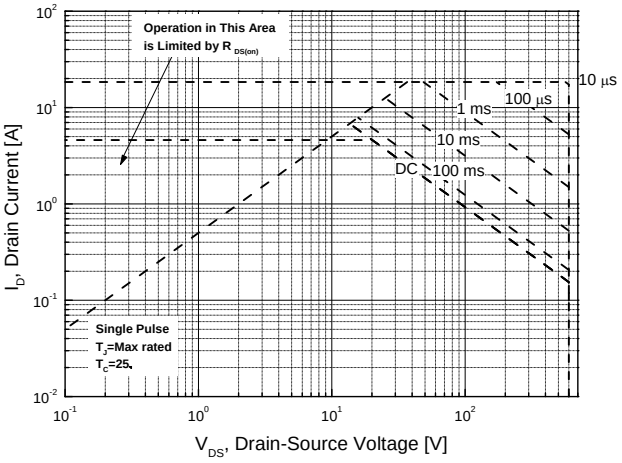


Fig.9 Maximum Safe Operating Area
MDP4N60 (TO-220)

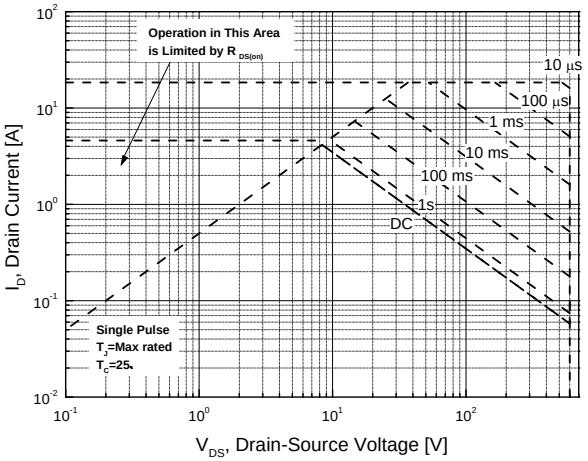


Fig.10 Maximum Safe Operating Area
MDF4N60 (TO-220F)

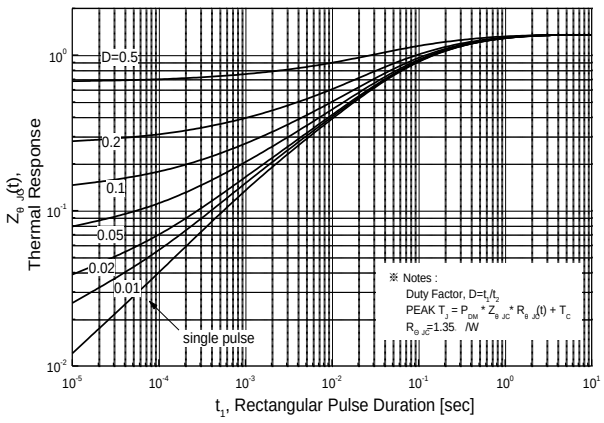


Fig.11 Transient Thermal Response Curve
MDP4N60 (TO-220)

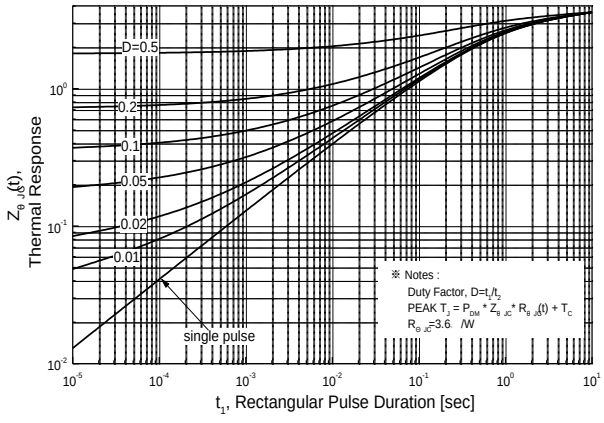


Fig.12 Transient Thermal Response Curve
MDF4N60 (TO-220F)

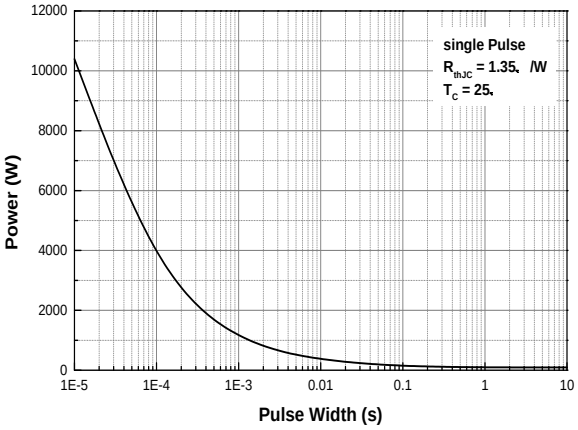


Fig.13 Single Pulse Maximum Power Dissipation MDP4N60 (TO-220)

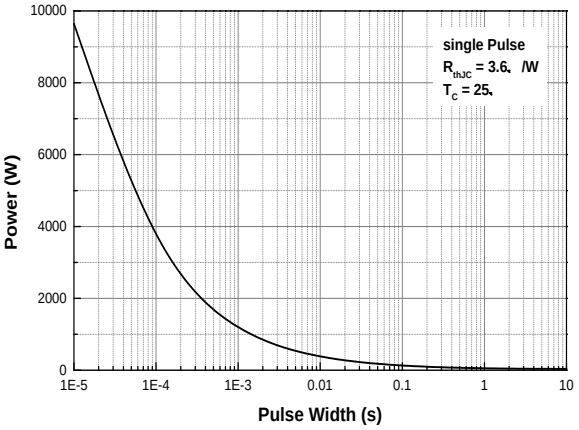


Fig.14 Single Pulse Maximum Power Dissipation MDF4N60 (TO-220F)

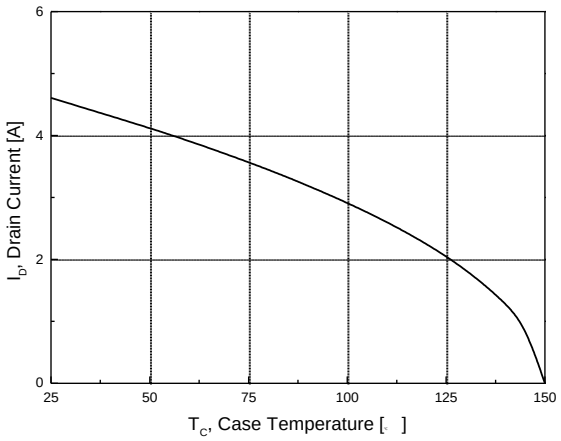
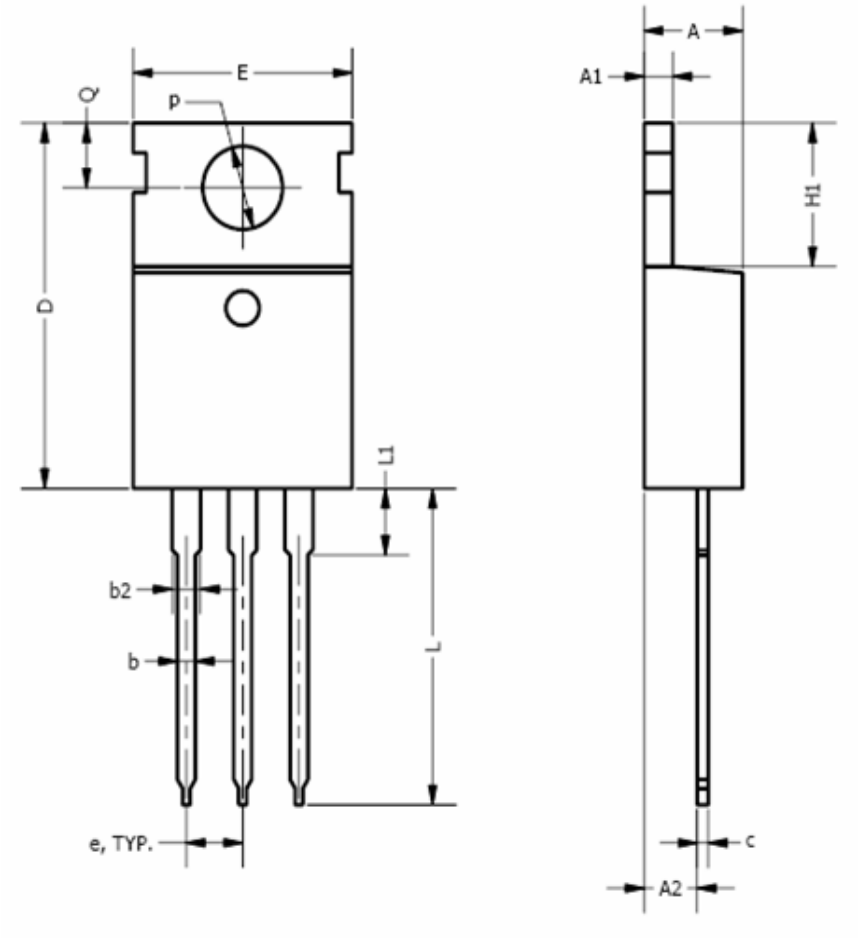


Fig.15 Maximum Drain Current vs. Case Temperature

Physical Dimensions

3 Leads, TO-220

Dimensions are in millimeters unless otherwise specified

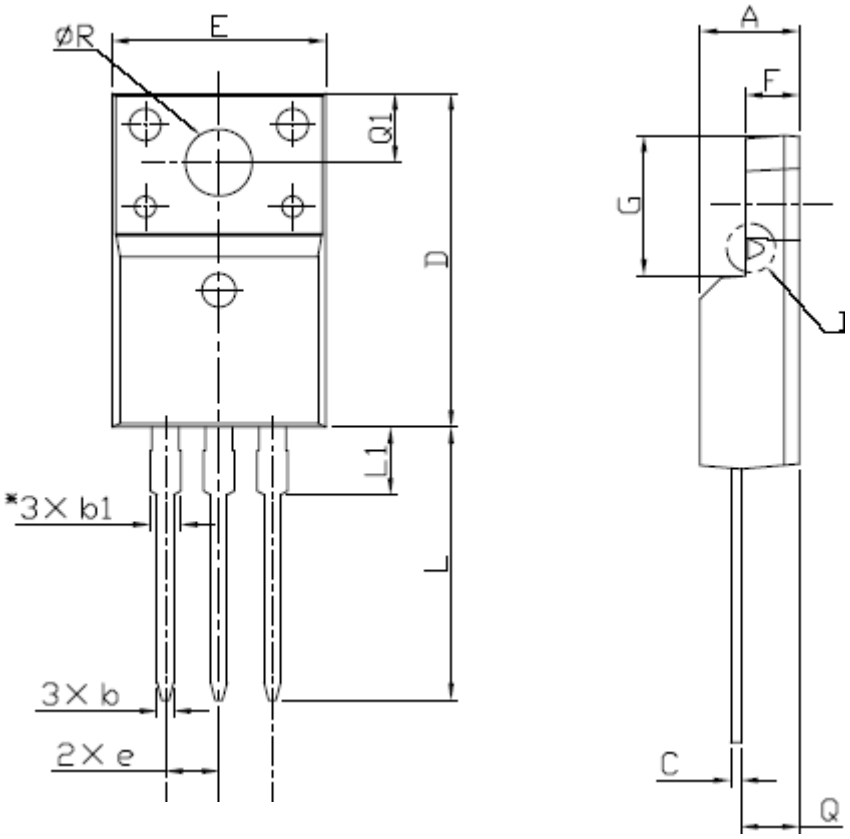


Symbol	Min	Nom	Max
A	3.56		4.83
A1	0.50		1.40
A2	2.03		2.92
b	0.38	0.69	1.02
b2	1.14	1.45	1.78
c	0.36		0.61
D	14.22		16.51
e	2.54 TYP		
E	9.65		10.67
H1	5.84		6.86
L	12.70		14.73
L1			6.35
ΦP	3.53		4.09
Q	2.54		3.43

Physical Dimensions

3 Leads, TO-220F

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	4.50		4.93
b	0.63		0.91
b1	1.15		1.47
C	0.33		0.63
D	15.47		16.13
E	9.60		10.71
e		2.54	
F	2.34		2.84
G	6.48		6.90
L	12.24		13.72
L1	2.79		3.67
Q	2.52		2.96
Q1	3.10		3.50
¢R	3.00		3.55